

< C band internally matched power GaAs FET >

MGFC44V4450

4.4 - 5.0 GHz BAND / 25W

DESCRIPTION

The MGFC44V4450 is an internally impedance-matched GaAs power FET especially designed for use in 4.4 - 5.0 GHz band amplifiers. The hermetically sealed metal-ceramic package guarantees high reliability.

FEATURES

- Internally matched to 50(ohm) system
- High output power
- P1dB=25W (TYP.) @f=4.4 5.0GHz
- High power gain
- GLP=11.0dB (TYP.) @f=4.4 5.0GHz • High power added efficiency
- P.A.E.=34% (TYP.) @f=4.4 5.0GHz • Low distortion [item -51]
- IM3=-45dBc (Typ.) @Po=33.5dBm S.C.L

APPLICATION

- item 01 : 4.4 5.0GHz band microwave high power amplifier
- item 51 : 4.4 5.0GHz band digital radio communication

QUALITY

• IG

RECOMMENDED BIAS CONDITIONS

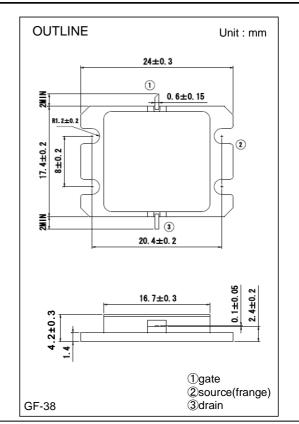
VDS=10V
ID=6.4A
RG=25ohm
Refer to Bias Procedure

Absolute maximum ratings (Ta=25°C)

Symbol	Parameter	Ratings	Unit
VGDO	Gate to drain breakdown voltage	-15	V
VGSO	Gate to source breakdown voltage	-15	V
ID	Drain current	20	А
IGR	Reverse gate current	-60	mA
IGF	Forward gate current	126	mA
PT *1	Total power dissipation	93	W
Tch	Cannel temperature	175	°C
Tstg *1 · Tc=25	Storage temperature	-65 to +175	°C

*1 : Tc=25°C

Electrical characteristics (Ta=25°C)



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Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Тур.	Max.	
IDSS	Saturated drain current	VDS=3V, VGS=0V	-	18	-	А
gm	Trans conductance	VDS=3V, ID=6.4A	-	6.5	-	S
VGS(off)	Gate to source cut-off voltage	VDS=3V,ID=120mA	-2	-	-5	V
P1dB	Output power at 1dB gain compression	VDS=10V,ID(RF off)=6.4A	43	-	-	dBm
GLP *2	Linear Power Gain	f=4.4 – 5.0GHz	10	-	-	dB
P.A.E.	Power added efficiency	Pin=23dBm *2	-	34	-	%
ID	Drain current		-	6.4	-	А
IM3 *3	3rd order IM distortion	7	-42	-	-	dBc
Rth(ch-c) *4	Thermal resistance	Delta Vf method	-	-	1.6	°C/W

*3 :item -51, 2 tone test, Po=33.5dBm Single Carrier Level ,f=5.0GHz, delta f=10MHz

*4 :Channel-case

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